

Status of defect investigations in Si and SiC

Wednesday 4 December 2024 14:10 (20 minutes)

We will present an overview of the on-going investigations of radiation induced defects in Si and SiC sensors performed within WG3 group.

Type of presentation (in-person/online)

in-person presentation

Type of presentation (I. scientific results or II. project proposal)

I. Presentation on scientific results

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Session Classification: WG3 - Radiation Damage